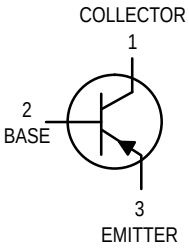
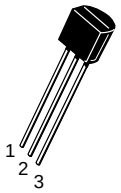
Amplifier Transistors

PNP Silicon

BC327,-16,-25
BC328,-16,-25





CASE 29–04, STYLE 17
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	BC327	BC328	Unit
Collector–Emitter Voltage	V_{CEO}	–45	–25	Vdc
Collector–Base Voltage	V_{CBO}	–50	–30	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current — Continuous	I_C	–800		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I_C = –10 mA, I_B = 0)	 BC327 BC328	$V_{(BR)CEO}$	 –45 –25	 — —	 — —	Vdc
Collector–Emitter Breakdown Voltage (I_C = –100 μA, I_E = 0)	 BC327 BC328	$V_{(BR)CES}$	 –50 –30	 — —	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = –10 μA, I_C = 0)		$V_{(BR)EBO}$	–5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = –30 V, I_E = 0) (V_{CB} = –20 V, I_E = 0)	 BC327 BC328	I_{CBO}	 — —	 — —	 –100 –100	nAdc
Collector Cutoff Current (V_{CE} = –45 V, V_{BE} = 0) (V_{CE} = –25 V, V_{BE} = 0)	 BC327 BC328	I_{CES}	 — —	 — —	 –100 –100	nAdc
Emitter Cutoff Current (V_{EB} = –4.0 V, I_C = 0)		I_{EBO}	—	—	–100	nAdc

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
(I_C = –100 mA, V_{CE} = –1.0 V)	BC327/BC328		100	—	630	
	BC327–16/BC328–16		100	—	250	
	BC327–25/BC328–25		160	—	400	
(I_C = –300 mA, V_{CE} = –1.0 V)			40	—	—	
Base–Emitter On Voltage (I_C = –300 mA, V_{CE} = –1.0 V)		$V_{BE(on)}$	—	—	–1.2	Vdc
Collector–Emitter Saturation Voltage (I_C = –500 mA, I_B = –50 mA)		$V_{CE(sat)}$	—	—	–0.7	Vdc
SMALL–SIGNAL CHARACTERISTICS						
Output Capacitance (V_{CB} = –10 V, I_E = 0, f = 1.0 MHz)		C_{ob}	—	11	—	pF
Current–Gain — Bandwidth Product (I_C = –10 mA, V_{CE} = –5.0 V, f = 100 MHz)		f_T	—	260	—	MHz

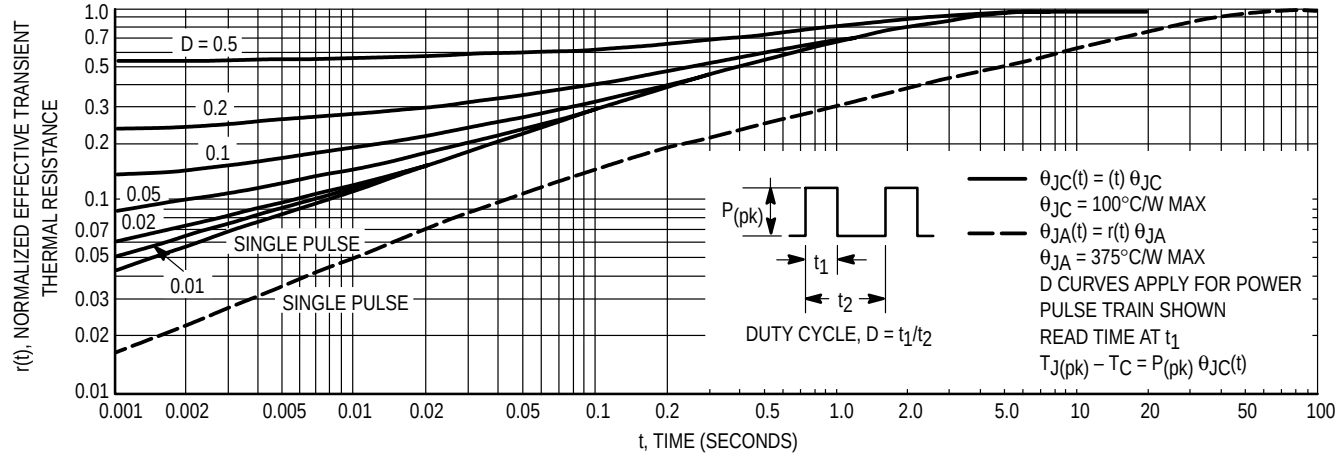


Figure 1. Thermal Response

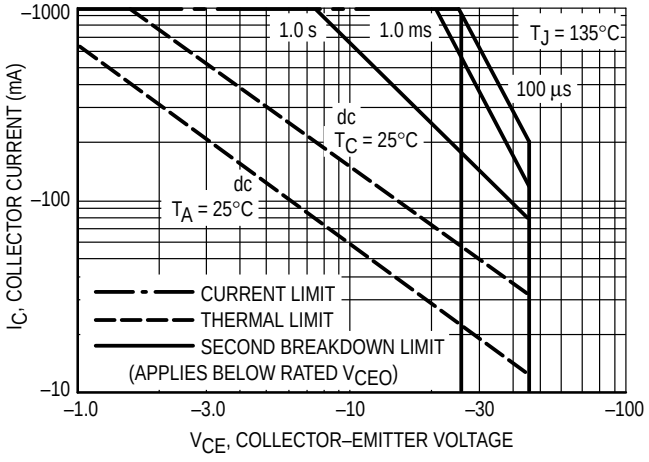


Figure 2. Active Region — Safe Operating Area

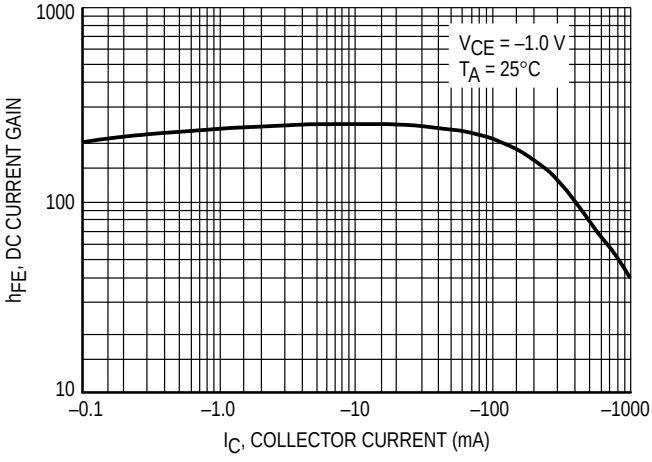


Figure 3. DC Current Gain

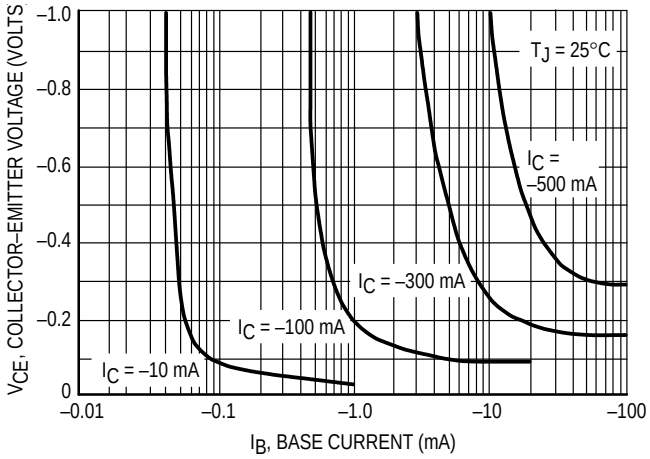


Figure 4. Saturation Region

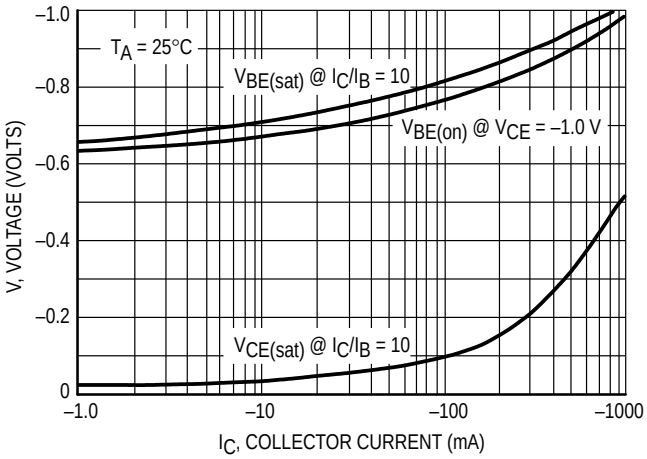


Figure 5. “On” Voltages

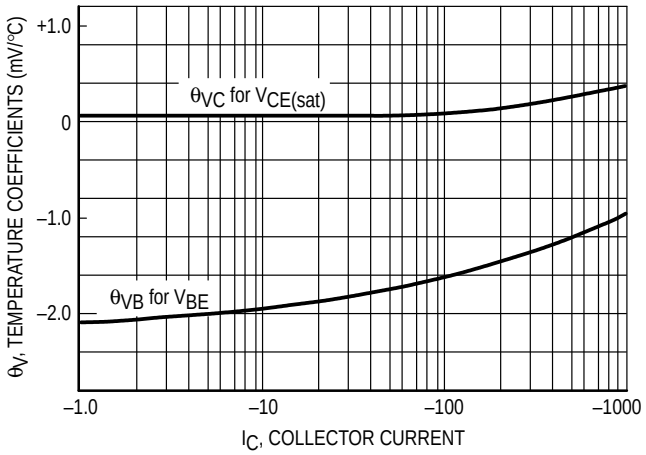


Figure 6. Temperature Coefficients

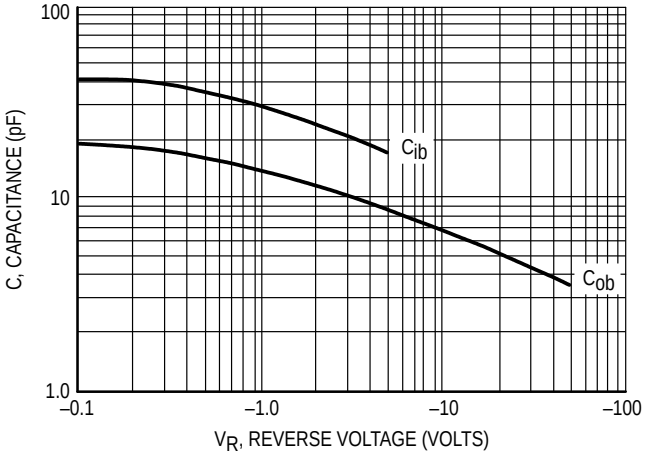
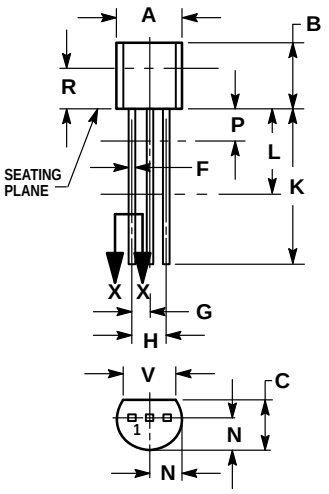
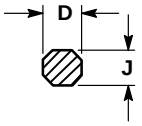


Figure 7. Capacitances

PACKAGE DIMENSIONS





SECTION X–X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

CASE 029–04
(TO–226AA)
ISSUE AD

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

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